

## **BAV102**; **BAV103**

# Single general-purpose switching diodes Rev. 03 — 16 August 2007

**Product data sheet** 

## **Product profile**

#### 1.1 General description

Single general-purpose switching diodes, fabricated in planar technology, and encapsulated in small hermetically sealed glass SOD80C Surface-Mounted Device (SMD) packages.

Table 1. **Product overview** 

Type number	Package		Configuration	
	NXP	JEITA		
BAV102	SOD80C	-	single	
BAV103				

#### 1.2 Features

- High switching speed:  $t_{rr} \le 50$  ns
- Low leakage current

- Low capacitance: C<sub>d</sub> ≤ 5 pF
- Small hermetically sealed glass SMD package

### 1.3 Applications

- High-speed switching
- General-purpose switching
- Voltage clamping
- Reverse polarity protection

#### 1.4 Quick reference data

Table 2. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
I <sub>F</sub>	forward current		[1][2]	-	-	250	mA
V <sub>R</sub>	reverse voltage						
	BAV102			-	-	150	V
	BAV103			-	-	200	V
t <sub>rr</sub>	reverse recovery time		[3]	-	-	50	ns

<sup>[1]</sup> Pulse test:  $t_p \le 300 \,\mu\text{s}$ ;  $\delta \le 0.02$ .



<sup>[2]</sup> Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

<sup>[3]</sup> When switched from  $I_F$  = 30 mA to  $I_R$  = 30 mA;  $R_L$  = 100  $\Omega$ ; measured at  $I_R$  = 3 mA.

## 2. Pinning information

Table 3. Pinning

	3		
Pin	Description	Simplified outline	Symbol
1	cathode	[1]	
2	anode	k	1 2
			006aab040

<sup>[1]</sup> The marking band indicates the cathode.

## 3. Ordering information

Table 4. Ordering information

Type number	Package		
	Name	Description	Version
BAV102	-	9.,	SOD80C
BAV103		2 connectors	

## 4. Marking

Table 5. Marking codes

Type number	Marking code <sup>[1]</sup>
BAV102	marking band
BAV103	_

<sup>[1]</sup> green: made in Philippines

## 5. Limiting values

Table 6. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{RRM}$	repetitive peak reverse voltage				
	BAV102		-	200	V
	BAV103		-	250	V
$V_R$	reverse voltage				
	BAV102		-	150	V
	BAV103		-	200	V
l <sub>F</sub>	forward current		[1][2] -	250	mA
I <sub>FRM</sub>	repetitive peak forward current		-	625	mA

Table 6. Limiting values ...continued

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
I <sub>FSM</sub>	non-repetitive peak	square wave	<u>[3]</u>		
	forward current	t <sub>p</sub> = 1 μs	-	9	Α
		$t_p = 100 \ \mu s$	-	3	Α
		t <sub>p</sub> = 1 s	-	1	Α
P <sub>tot</sub>	total power dissipation	$T_{amb} \le 25  ^{\circ}C$	[2] _	400	mW
T <sub>j</sub>	junction temperature		-	175	°C
T <sub>amb</sub>	ambient temperature		-65	+175	°C
T <sub>stg</sub>	storage temperature		-65	+175	°C

<sup>[1]</sup> Pulse test:  $t_p \le 300 \ \mu s; \ \delta \le 0.02$ .

### 6. Thermal characteristics

Table 7. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	<u>[1]</u> -	-	375	K/W
$R_{th(j-t)}$	thermal resistance from junction to tie-point		-	-	300	K/W

<sup>[1]</sup> Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

## 7. Characteristics

 Table 8.
 Characteristics

 $T_{amb}$  = 25 °C unless otherwise specified.

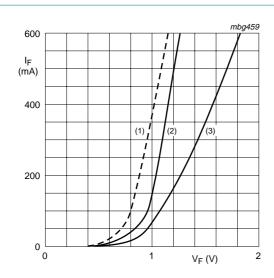
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{F}$	forward voltage		<u>[1]</u>			
		$I_F = 100 \text{ mA}$	-	-	1.0	V
		$I_F = 200 \text{ mA}$	-	-	1.25	V
$I_R$	reverse current					
	BAV102	V <sub>R</sub> = 150 V	-	-	100	nΑ
		$V_R = 150 \text{ V}; T_j = 150 ^{\circ}\text{C}$	-	-	100	μΑ
	BAV103	V <sub>R</sub> = 200 V	-	-	100	nA
		$V_R = 200 \text{ V}; T_j = 150 ^{\circ}\text{C}$	-	-	100	μΑ
C <sub>d</sub>	diode capacitance	$f = 1 MHz; V_R = 0 V$	-	-	5	pF
t <sub>rr</sub>	reverse recovery time		[2] _	-	50	ns

<sup>[1]</sup> Pulse test:  $t_p \le 300 \ \mu s; \ \delta \le 0.02$ .

<sup>[2]</sup> Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

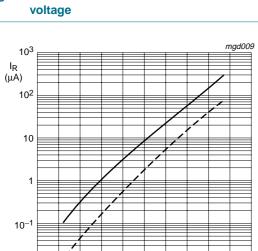
<sup>[3]</sup>  $T_i = 25$  °C prior to surge.

<sup>[2]</sup> When switched from  $I_F$  = 30 mA to  $I_R$  = 30 mA;  $R_L$  = 100  $\Omega$ ; measured at  $I_R$  = 3 mA.



- (1)  $T_{amb} = 150 \,^{\circ}C$ ; typical values
- (2)  $T_{amb} = 25 \,^{\circ}C$ ; typical values
- (3)  $T_{amb} = 25 \,^{\circ}C$ ; maximum values

Fig 1. Forward current as a function of forward voltage



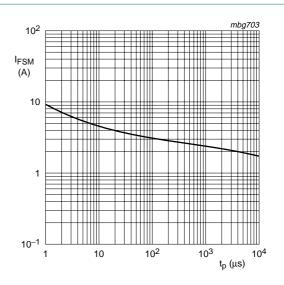
 $V_R = V_{Rmax}$ 

 $10^{-2}$ 

Solid line: maximum values

Dotted line: typical values

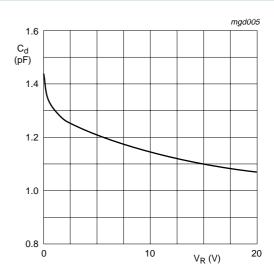
Fig 3. Reverse current as a function of junction temperature



Based on square wave currents.

 $T_i = 25$  °C; prior to surge

Fig 2. Non-repetitive peak forward current as a function of pulse duration; maximum values

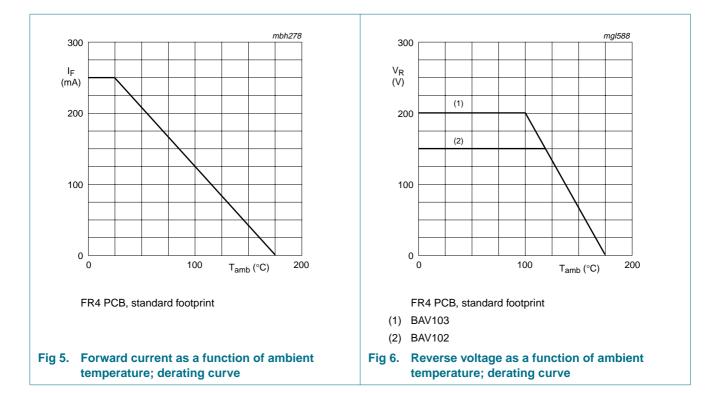


 $f = 1 \text{ MHz}; T_{amb} = 25 \, ^{\circ}\text{C}$ 

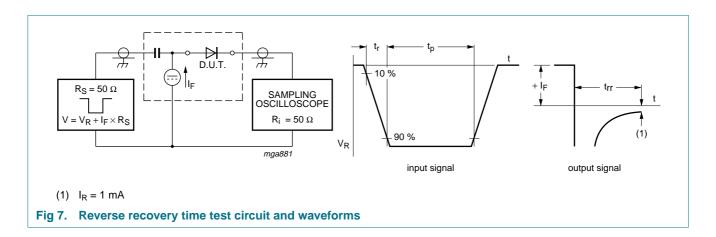
Fig 4. Diode capacitance as a function of reverse voltage; typical values

200

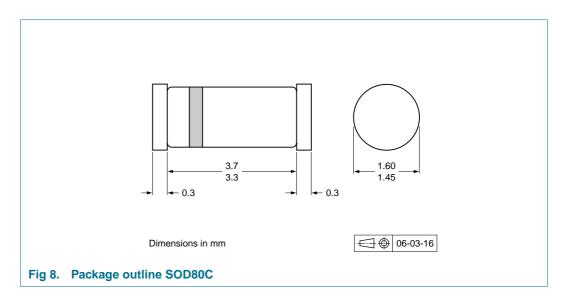
T<sub>j</sub> (°C)



## 8. Test information



## 9. Package outline



## 10. Packing information

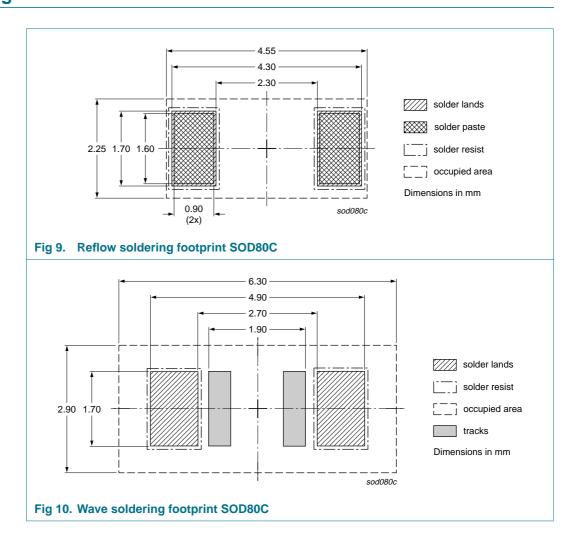
Table 9. Packing methods

The indicated -xxx are the last three digits of the 12NC ordering code.[1]

Type number	Package	age Description		Packing quantity		
				2500	10000	
BAV102	SOD80C	4 mm pitch, 8 mm tape and reel		-115	-135	
BAV103						

[1] For further information and the availability of packing methods, see Section 14.

## 11. Soldering



## 12. Revision history

### Table 10. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes	
BAV102_BAV103_3	20070816	Product data sheet	-	BAV100_2	
Modifications:		of this data sheet has been of NXP Semiconductors.	redesigned to comply v	vith the new identity	
	<ul> <li>Legal texts</li> </ul>	<ul> <li>Legal texts have been adapted to the new company name where appropriate.</li> </ul>			
	<ul> <li>Type number</li> </ul>	<ul> <li>Type numbers BAV100 and BAV101 have been removed</li> </ul>			
	<ul> <li>Section 1.1</li> </ul>	Section 1.1 "General description": amended			
	Table 1 "Product overview": added				
	Table 2 "Quick reference data": added				
	Section 3 "Ordering information": added				
	• Figure 7: fig	gure title amended			
	• Figure 8: su	perseded by minimized pa	ckage outline drawing		
	• Section 10	"Packing information": adde	ed		
	Section 11	"Soldering": added			
	Section 13	"Legal information": update	d		
BAV100_2	19960917	Product specification	-	BAV100_1	
BAV100_1	19960423	Product specification	-	-	

## 13. Legal information

#### 13.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
- [3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL <a href="http://www.nxp.com">http://www.nxp.com</a>.

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